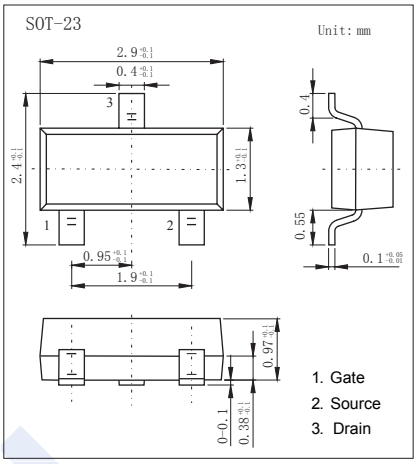
P-Channel MOSFET

KI007P



■ Features

- V_{DS} (V) =-12V
- I_D =-3.5 A
- $R_{DS(ON)}$ < 65mΩ (V_{GS} =-4.5V , I_D=-1A)
- $R_{DS(ON)}$ < 100mΩ (V_{GS} =-2.5V , I_D=-0.5A)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current @ T_J=25℃	I_D	3.5	A
Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	℃
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-12			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-12V, V_{GS}=0V,T_J=25℃			-1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±12V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.5		-1.3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-1A			65	mΩ
		V_{GS}=-2.5V, I_D=-0.5A			100	
		V_{GS}=-4.5V, I_D=-3A			77	
		V_{GS}=-2.5V, I_D=-2A			120	

■ Marking

Marking	007P